

SPECIFICATION OF LED CHIP

CP940-40

[INFRARED]

1) Commodity Type and Physical Characteristics.

- 1. Material GaAlAs/GaAs
- 2. Electrode Top Side N (cathode) side : Au Alloy
Bottom Side P (anode) side : Au Alloy
- 3. Electrode Pattern Fig.1
- 4. Chip Size Fig.2
- 5. Chip Thickness Fig.2
- 6. Emission Area Fig.2

2) Electro-Optical Characteristics

Parameters	Symbol	Condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		1.22	1.35	V
		If=50mA		1.25	1.45	
Power Intensity	Po	If=20mA	1.5	2.5		mW
		If=50mA	3.8	6.2		
Reverse Current	Ir	Vr=5V			10	uA
Spectral Radiation Bandwidth	$\Delta\lambda$	If=20mA		50		nm
RiseTime	tr	If=20mA		1000		ns
FallTime	tf	If=20mA		500		ns

‡ Die shall be mounted on TO=18 gold header without resin coated. (Ta=25°C)

[Unit: um]

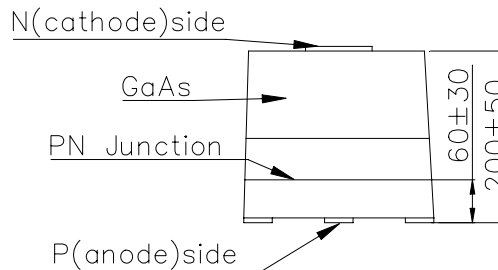
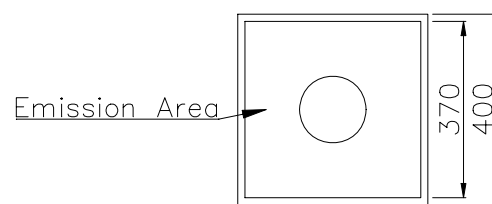
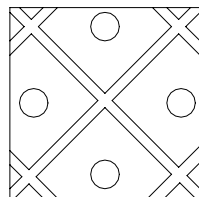
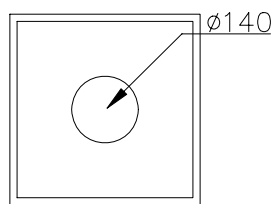


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area